

TOSHIBA GTR Module Silicon N Channel IGBT

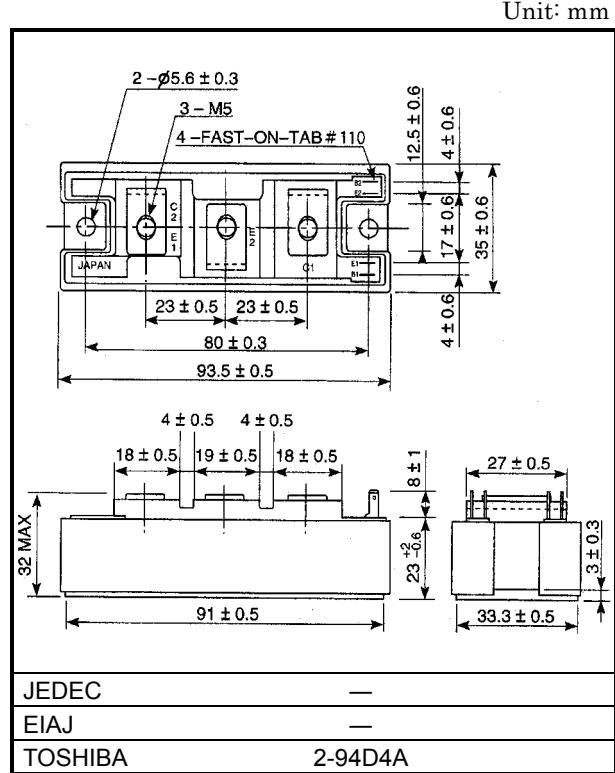
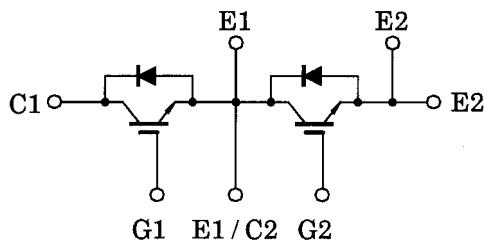
# MG50Q2YS50

High Power Switching Applications

Motor Control Applications

- High input impedance
- High speed :  $t_f = 0.3\mu s$  (Max)  
@Inductive load
- Low saturation voltage  
:  $V_{CE}(\text{sat}) = 3.6V$  (Max)
- Enhancement-mode
- Includes a complete half bridge in one package.
- The electrodes are isolated from case.

## Equivalent Circuit



## Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		$V_{CES}$	1200	V
Gate-emitter voltage		$V_{GES}$	±20	V
Collector current	DC	$I_C$ ( $25^\circ C / 80^\circ C$ )	78 / 50	A
	1ms	$I_{CP}$ ( $25^\circ C / 80^\circ C$ )	156 / 100	
Forward current	DC	$I_F$	50	A
	1ms	$I_{FM}$	100	
Collector power dissipation ( $T_c = 25^\circ C$ )		$P_C$	400	W
Junction temperature		$T_j$	150	°C
Storage temperature range		$T_{stg}$	-40 ~ 125	°C
Isolation voltage		$V_{Isol}$	2500 (AC 1 minute)	V
Screw torque (Terminal / mounting)		—	3 / 3	N·m

Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{V}, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector cut-off current	$I_{CES}$	$V_{CE} = 1200\text{V}, V_{GE} = 0$	—	—	1.0	mA
Gate-emitter cut-off voltage	$V_{GE}(\text{OFF})$	$I_C = 50\text{mA}, V_{CE} = 5\text{V}$	3.0	—	6.0	V
Collector-emitter saturation voltage	$V_{CE}(\text{sat})$	$I_C = 50\text{A}, V_{GE} = 15\text{V}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	—	2.8	3.6	V
Input capacitance	$C_{ies}$	$V_{CE} = 10\text{V}, V_{GE} = 0, f = 1\text{MHz}$	—	6.0	—	nF
Switching time	Turn-on delay time	$t_d(\text{on})$	—	0.05	—	$\mu\text{s}$
	Rise time	$t_r$	Inductive load $V_{CC} = 600\text{V}$ $I_C = 50\text{A}$ $V_{GE} = \pm 15\text{V}$ $R_G = 24\Omega$	—	0.05	
	Turn-on time	$t_{on}$	(Note 1)	—	0.2	
	Turn-off delay time	$t_d(\text{off})$		—	0.5	
	Fall time	$t_f$		—	0.1	
	Turn-off time	$t_{off}$		—	0.6	
Forward voltage	$V_F$	$I_F = 50\text{ A}, V_{GE} = 0$	—	2.4	3.5	V
Reverse recovery time	$t_{rr}$	$I_F = 50\text{ A}, V_{GE} = -10\text{ V}, di/dt = 700\text{ A}/\mu\text{s}$	—	0.1	0.25	$\mu\text{s}$
Thermal resistance	$R_{th(j-c)}$	Transistor stage	—	—	0.31	$^\circ\text{C}/\text{W}$
		Diode stage	—	—	0.94	

Note 1: Switching time and reverse recovery time test circuit &amp; timing chart

